

isc Thyristors

2P4M-D

**DESCRIPTION**

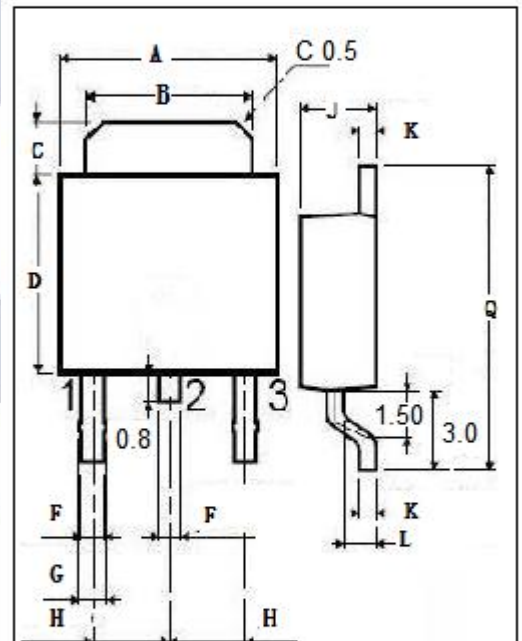
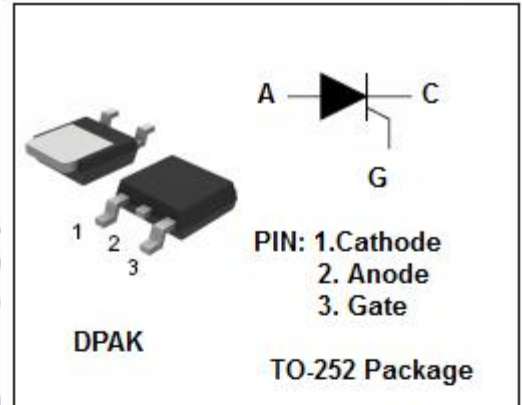
- The 2P4M is P-gate all diffused plastic molded type SCR granted average on-state current 2A( $T_C=77^\circ\text{C}$ )
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

**APPLICATIONS**

- Highly sensitive triggering levels
- Solid state switches etc
- Automatic gas lighter, battery charger
- For capacitive discharge ignitions, motor control in kitchen aids, over voltage crowbar protection in low power supplies applications.

**ABSOLUTE MAXIMUM RATINGS( $T_a=25^\circ\text{C}$ )**

SYMBOL	PARAMETER	MIN	UNIT
$V_{DRM}$	Repetitive peak off-state voltage	400	V
$V_{RRM}$	Repetitive peak reverse voltage	400	V
$I_{T(AV)}$	On-state current 180° conduction angle	2	A
$I_{TSM}$	Non-repetitive surge peak on-state current $t=20\text{ms}$	20	A
$P_{G(AV)}$	Average gate power dissipation $T_j = 125^\circ\text{C}$	0.1	W
$T_j$	Junction temperature	125	°C
$T_{stg}$	Storage temperature	-40 to +150	°C



DIM	mm	
	MIN	MAX
A	6.40	6.60
B	5.20	5.40
C	1.15	1.35
D	5.70	6.10
F	0.65	
G	0.75	
H	2.10	2.50
J	2.10	2.40
K	0.40	0.60
L	0.90	1.10
Q	9.90	10.1

**isc Thyristors****2P4M-D****ELECTRICAL CHARACTERISTICS (T<sub>c</sub>=25°C unless otherwise specified)**

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
I <sub>RRM</sub>	Repetitive peak reverse current	V <sub>RM</sub> =V <sub>RRM</sub> , R <sub>GK</sub> =1k Ω, T <sub>j</sub> =125°C		100	μ A
I <sub>DRM</sub>	Repetitive peak off-state current	V <sub>DM</sub> =V <sub>DRM</sub> , R <sub>GK</sub> =1k Ω, T <sub>j</sub> =125°C		100	μ A
V <sub>TM</sub>	On-state voltage	I <sub>TM</sub> = 4A		2.2	V
I <sub>GT</sub>	Gate-trigger current	V <sub>DM</sub> =6V; R <sub>L</sub> =100 Ω		200	μ A
V <sub>GT</sub>	Gate-trigger voltage	V <sub>DM</sub> =6V; R <sub>L</sub> =100 Ω		0.8	V